



STS17NH3LL

N-channel 30V - 0.004Ω - 17A - SO-8
STripFET™ Power MOSFET for DC-DC conversion

General features

Type	V _{DSS}	R _{DS(on)}	I _D
STS17NH3LL	30V	<0.0057Ω	17A ⁽¹⁾

1. This value is rated according to R_{thj-pcb}

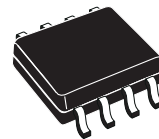
- Optimal R_{DS(on)} x Q_g trade-off @ 4.5 V
- Conduction losses reduced
- Improved junction-case thermal resistance
- Low threshold device

Description

This device utilizes the latest advanced design rules of ST's proprietary STripFET™ technology. This process coupled to unique metallization techniques realizes the most advanced low voltage Power MOSFET in SO-8 ever produced.

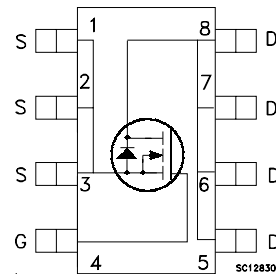
Applications

- Switching application



SO-8

Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STS17NH3LL	17H3LL-	SO-8	Tape & reel

Contents

1 **Electrical ratings** 3

2 **Electrical characteristics** 4

 2.1 Electrical characteristics (curves) 6

3 **Test circuit** 8

4 **Package mechanical data** 9

5 **Revision history** 11

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	30	V
V_{GS}	Gate- source voltage	± 16	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	17	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	10.6	A
$I_{DM}^{(2)}$	Drain current (pulsed)	68	A
$P_{tot}^{(1)}$	Total dissipation at $T_C = 25^\circ\text{C}$	2.7	W
T_{stg}	Storage temperature	-55 to 150	$^\circ\text{C}$
T_j	Operating junction temperature		

1. This value is rated according to $R_{thj-pcb}$
2. Pulse width limited by safe operating area

Table 2. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-ambient max	47	$^\circ\text{C/W}$

1. When mounted on 1inch² FR-4 board, 2oz of Cu and $t < 10\text{sec}$

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 250 µA, V _{GS} = 0	30			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V _{DS} = Max rating V _{DS} = Max rating @ 125°C			1 10	µA µA
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ± 16V			±100	nA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250µA	1			V
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10V, I _D = 8.5A V _{GS} = 4.5V, I _D = 8.5A		0.004 0.005	0.0057 0.0075	Ω Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V _{DS} =25V, f=1MHz, V _{GS} = 0		1810 565 41		pF pF pF
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	V _{DD} =15V, I _D =17A V _{GS} =4.5V (see Figure 13)		18 4.8 5.3	24	nC nC nC
R _G	Gate input resistance	f=1 MHz Gate DC Bias = 0 Test signal level = 20mV open drain	0.5	1.5	3	Ω

Table 5. Switching times

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	$V_{DD} = 15V$, $I_D = 8.5A$ $R_G = 4.7\Omega$, $V_{GS} = 10V$ (see Figure 15)		8 65		ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time	$V_{DD} = 15V$, $I_D = 8.5A$ $R_G = 4.7\Omega$, $V_{GS} = 10V$ (see Figure 15)		38 20		ns ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				17	A
I_{SDM}	Source-drain current (pulsed)				68	A
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = 17A$, $V_{GS} = 0$			1.3	V
t_{rr}	Reverse recovery time	$I_{SD} = 17A$, $di/dt = 100A/\mu s$		22		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 15V$, $T_j = 25^\circ C$		32		nC
I_{RRM}	Reverse recovery current	(see Figure 14)		1.9		A

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

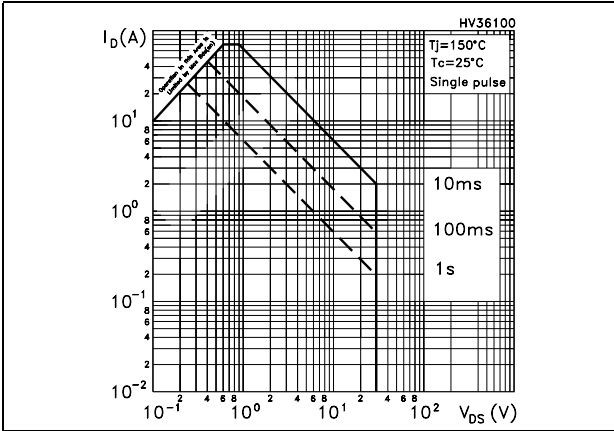


Figure 2. Thermal impedance

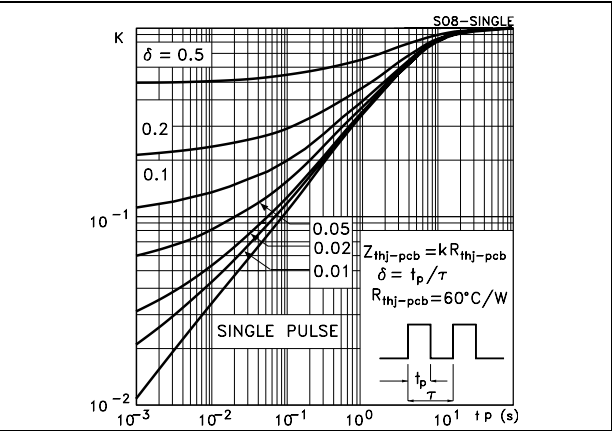


Figure 3. Output characteristics

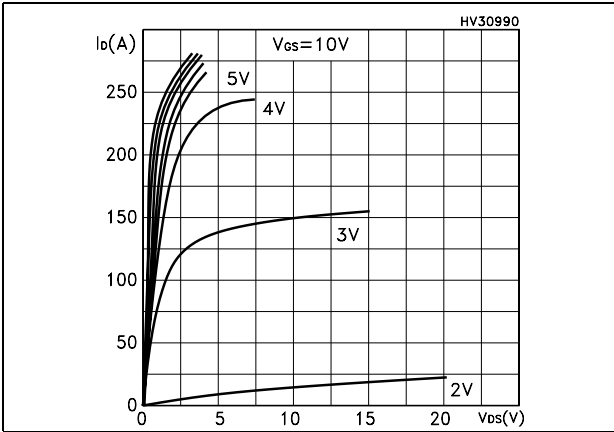


Figure 4. Transfer characteristics

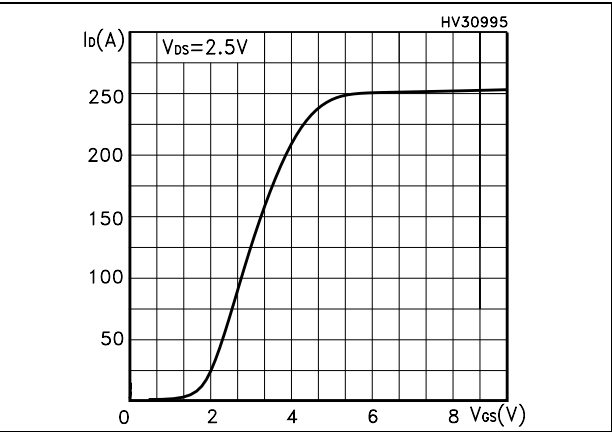


Figure 5. Normalized $B_{V_{DS}}$ vs temperature

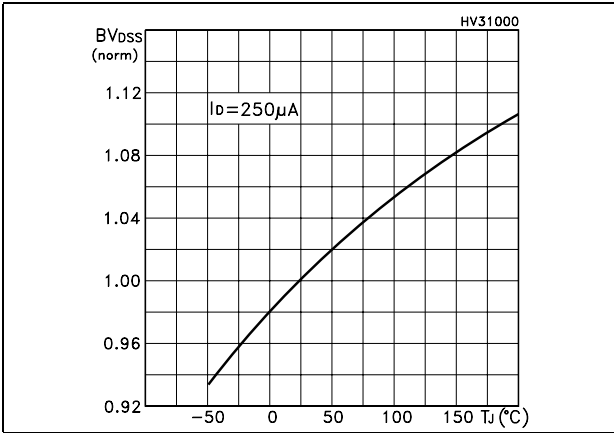


Figure 6. Static drain-source on resistance

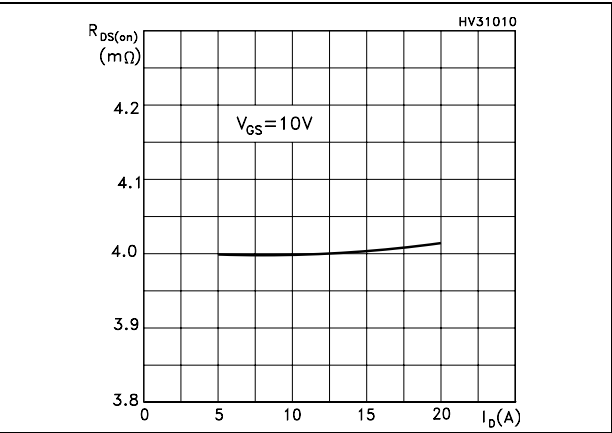


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

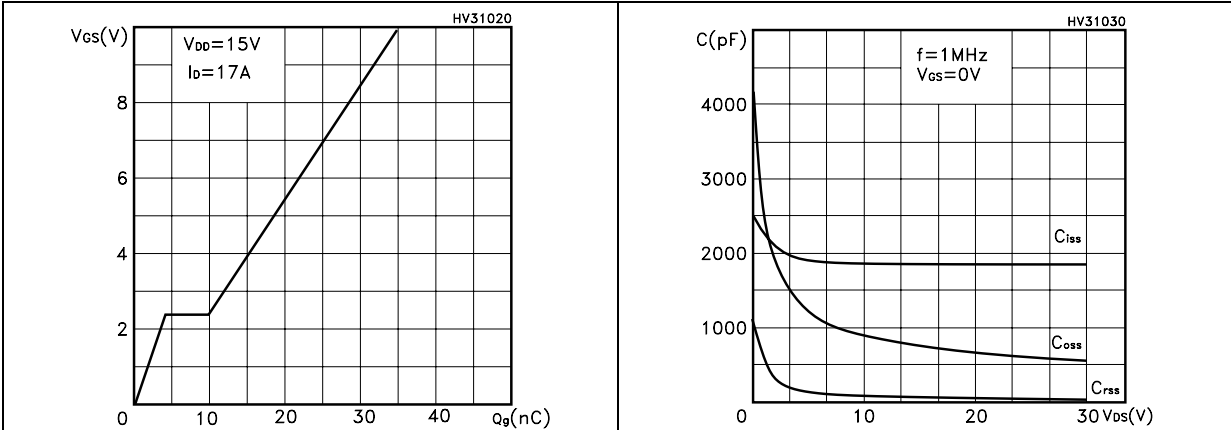


Figure 9. Normalized gate threshold voltage vs temperature Figure 10. Normalized on resistance vs temperature

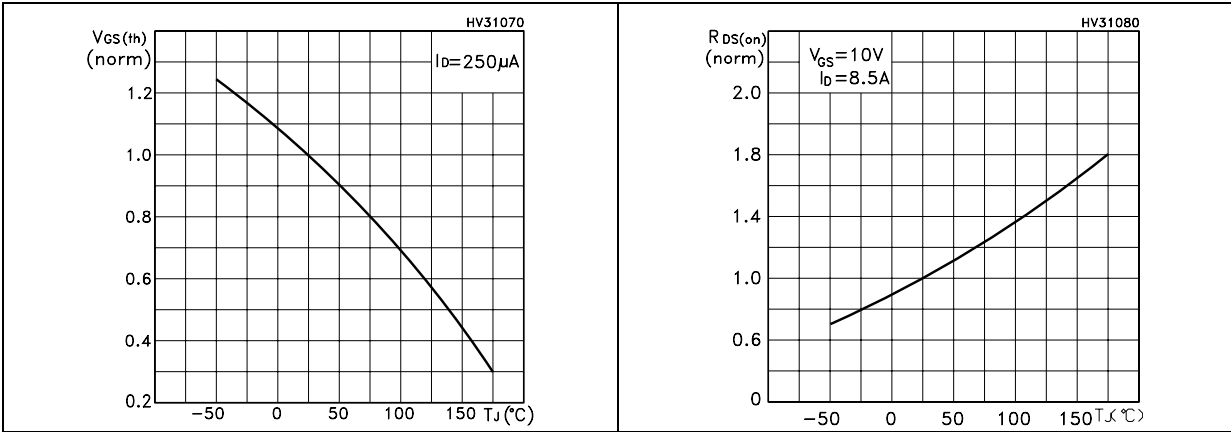
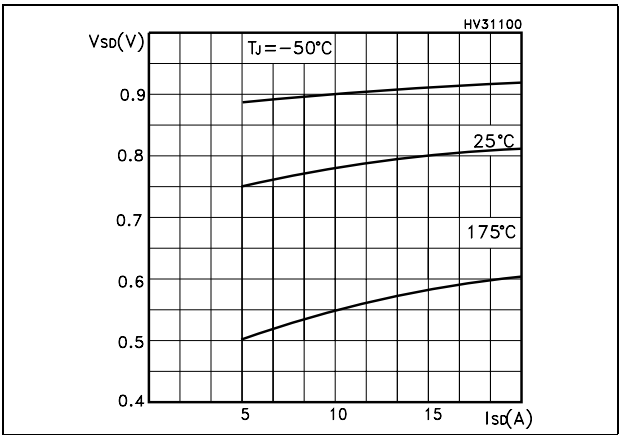


Figure 11. Source-drain diode forward characteristics



3 Test circuit

Figure 12. Switching times test circuit for resistive load

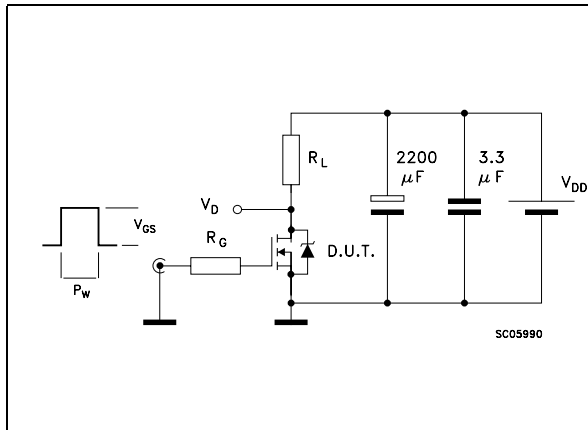


Figure 13. Gate charge test circuit

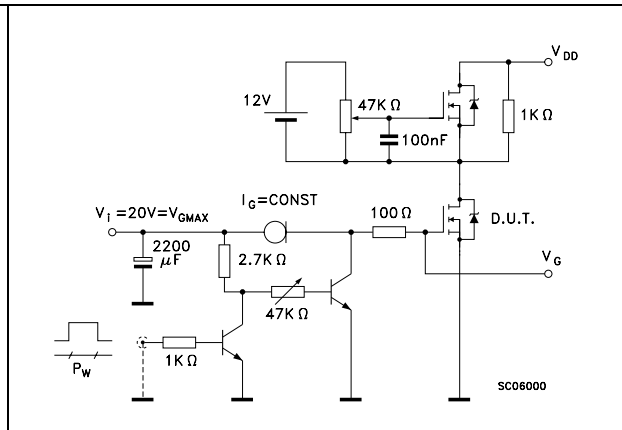


Figure 14. Test circuit for inductive load switching and diode recovery times

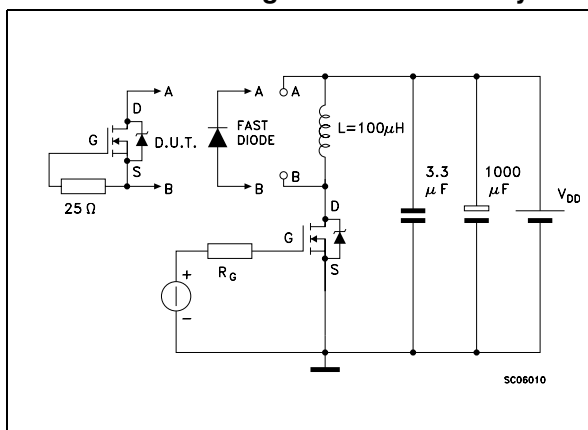


Figure 15. Unclamped inductive load test circuit

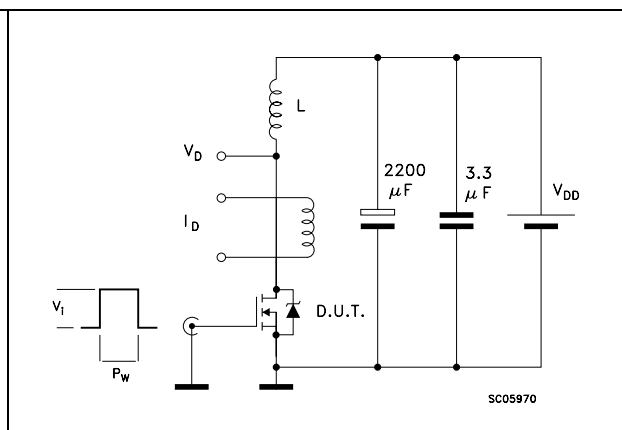


Figure 16. Unclamped inductive waveform

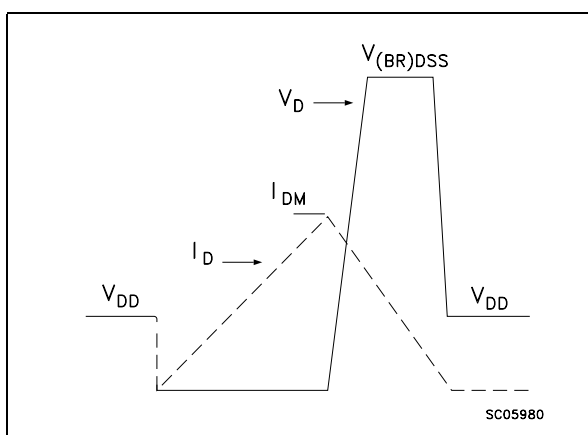
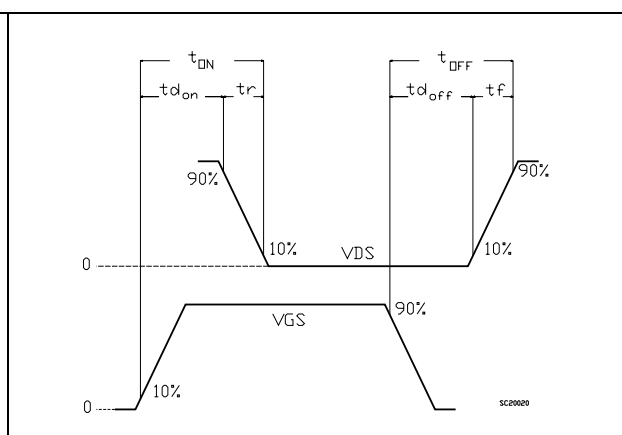


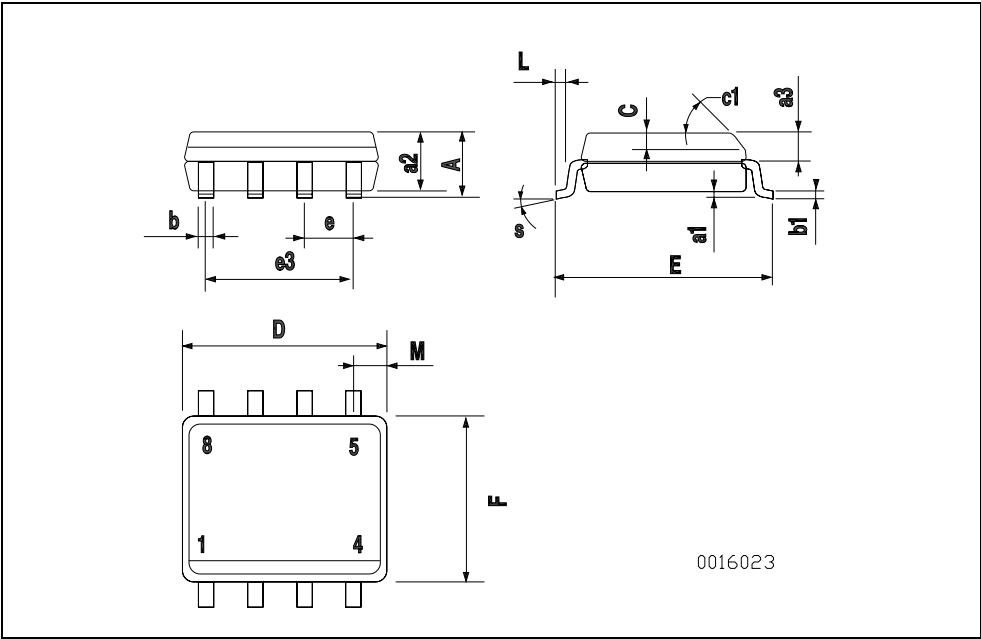
Figure 17. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

SO-8 MECHANICAL DATA						
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					



5 Revision history

Table 7. Revision history

Date	Revision	Changes
01-Aug-2006	1	First release
09-Jan-2007	2	Complete version

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2007 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com